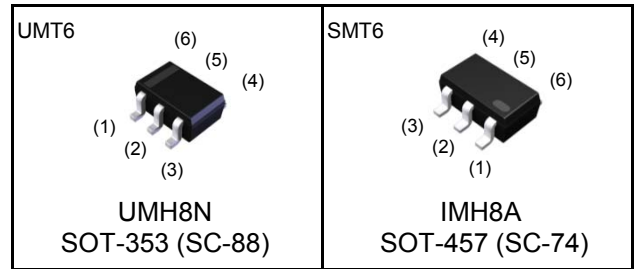


Parameter	Tr1 and Tr2
$V_{CEO}$	50V
$I_C$	100mA
$R_1$	10k $\Omega$

### ●Outline



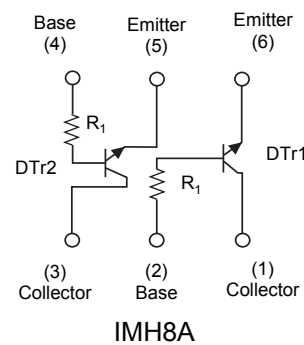
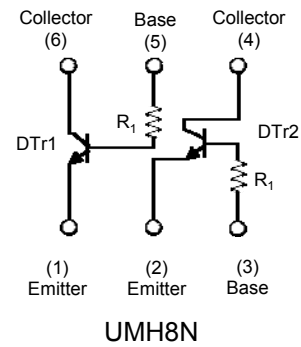
### ●Features

- 1) Built-In Biasing Resistors.
- 2) Two DTC114T chips in one package.
- 3) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 4) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 5) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 6) Lead Free/RoHS Compliant.

### ●Application

Inverter circuit, Interface circuit, Driver circuit

### ●Inner circuit



### ●Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
UMH8N	UMT6	2021	TN	180	8	3,000	H8
IMH8A	SMT6	2928	T110	180	8	3,000	H8

●Absolute maximum ratings (Ta = 25°C)

<For DTr1 and DTr2 in common>

Parameter	Symbol	Values	Unit	
Collector-base voltage	$V_{CBO}$	50	V	
Collector-emitter voltage	$V_{CEO}$	50	V	
Emitter-base voltage	$V_{EBO}$	5	V	
Collector current	$I_C^{*1}$	100	mA	
Collector Power dissipation	UMH8N	$P_D^{*2}$	150 (Total) <sup>*3</sup>	mW
	IMH8A		300 (Total) <sup>*4</sup>	mW
Junction temperature	$T_j$	150	°C	
Range of storage temperature	$T_{stg}$	-55 to +150	°C	

●Electrical characteristics (Ta = 25°C)

<For DTr1 and DTr2 in common>

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Collector-base breakdown voltage	$BV_{CBO}$	$I_C = 50\mu A$	50	-	-	V
Collector-emitter breakdown voltage	$BV_{CEO}$	$I_C = 1mA$	50	-	-	V
Emitter-base breakdown voltage	$BV_{EBO}$	$I_E = 50\mu A$	5	-	-	V
Collector cut-off current	$I_{CBO}$	$V_{CB} = 50V$	-	-	0.5	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 4V$	-	-	0.5	$\mu A$
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C / I_B = 10mA / 1mA$	-	-	0.3	V
DC current gain	$h_{FE}$	$V_{CE} = 5V, I_C = 1mA$	100	250	600	-
Input resistance	$R_1$	-	7	10	13	k $\Omega$
Transition frequency	$f_T^{*1}$	$V_{CE} = 10V, I_E = -5mA$ $f = 100MHz$	-	250	-	MHz

\*1 Characteristics of built-in transistor

\*2 Each terminal mounted on a reference footprint

\*3 120mW per element must not be exceeded.

\*4 200mW per element must not be exceeded.

●Electrical characteristic curves (Ta = 25°C) <For DTr1 and DTr2 in common>

Fig.1 Grounded emitter propagation characteristics

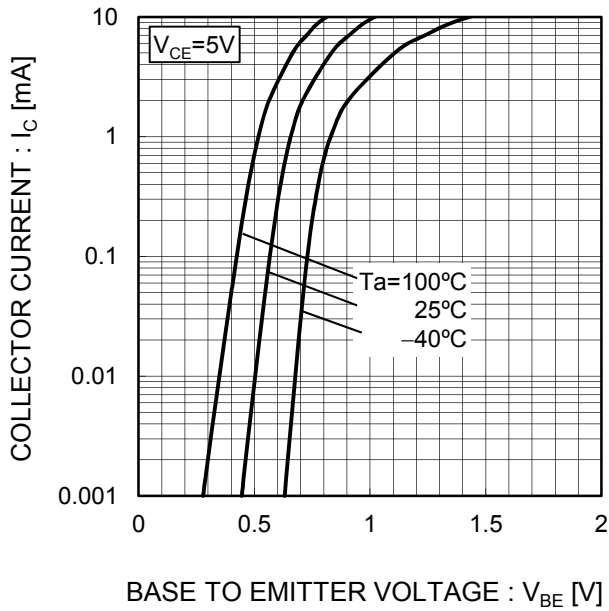


Fig.2 Grounded emitter output characteristics  $I_B = 500\mu A$

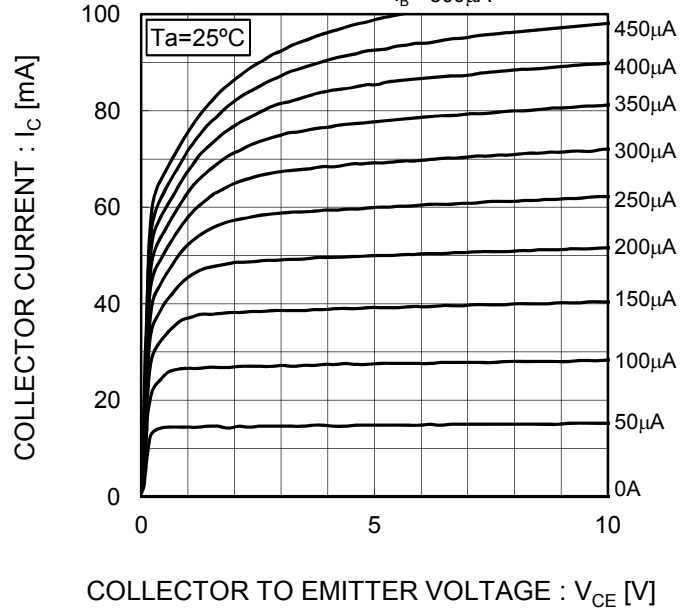


Fig.3 DC Current gain vs. Collector Current

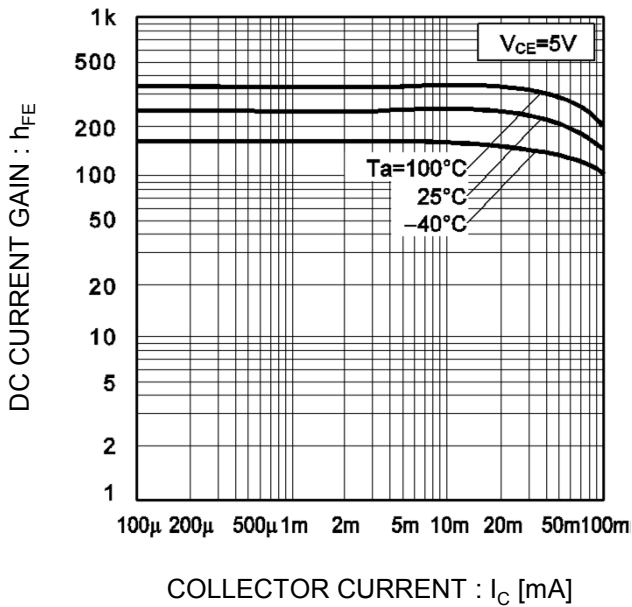
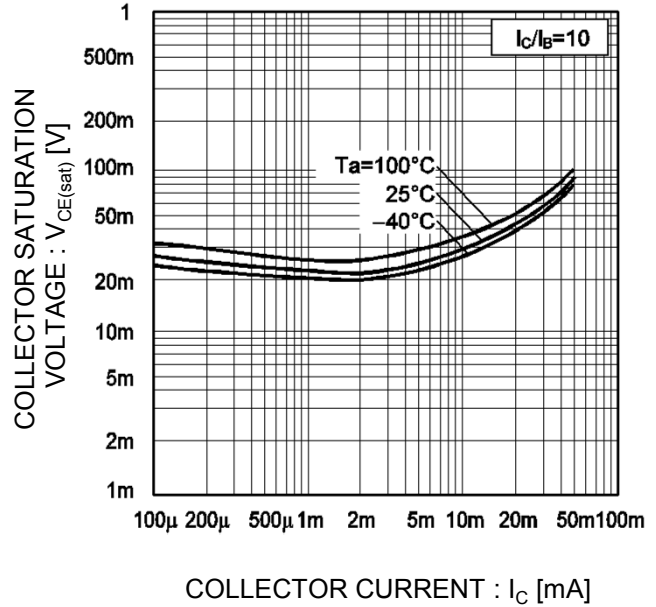
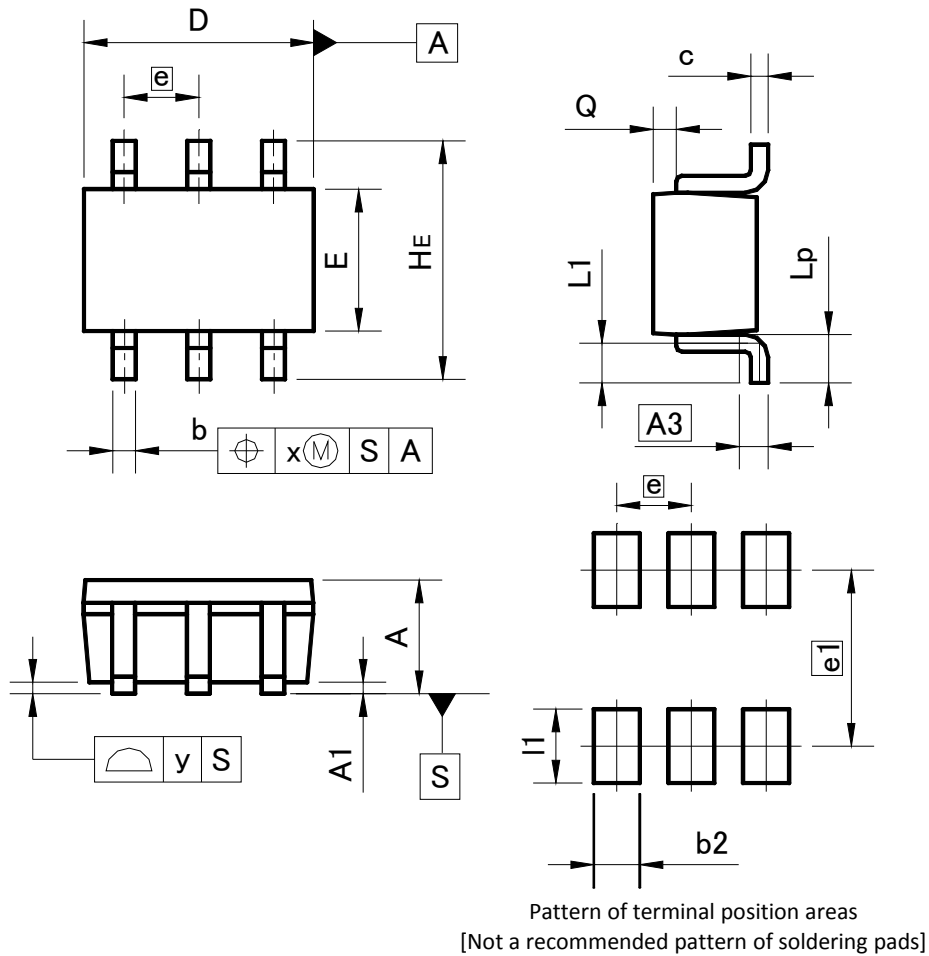


Fig.4 Collector-emitter saturation voltage vs. Collector Current



●Dimensions (Unit : mm)

UMT6



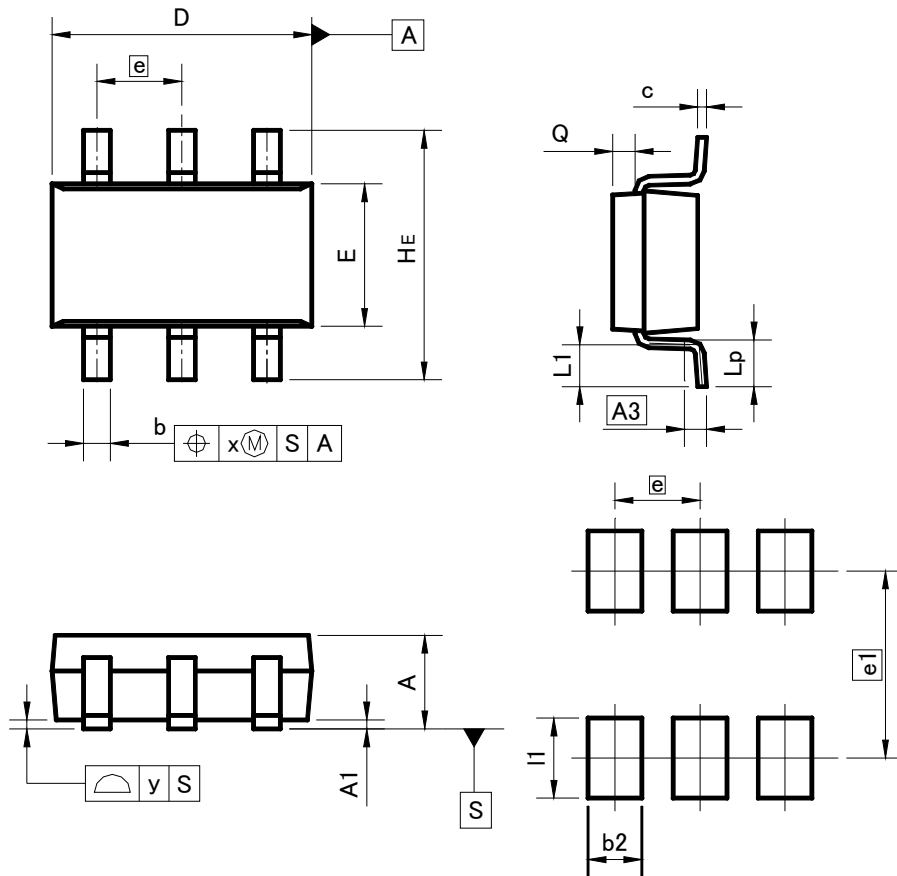
DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.80	1.00	0.031	0.039
A1	0.00	0.10	0.000	0.004
A3	0.25		0.010	
b	0.15	0.30	0.006	0.012
c	0.10	0.20	0.004	0.008
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
e	0.65		0.026	
HE	2.00	2.20	0.079	0.087
L1	0.20	0.50	0.008	0.020
Lp	0.25	0.55	0.010	0.022
Q	0.10	0.30	0.004	0.012
x	-	0.10	-	0.004
y	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.40	-	0.016
e1	1.55		0.061	
l1	-	0.65	-	0.026

Dimension in mm / inches

●Dimensions (Unit : mm)

SMT6



Pattern of terminal position areas  
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.00	1.30	0.039	0.051
A1	0.00	0.10	0.000	0.004
A3	0.25		0.010	
b	0.25	0.40	0.010	0.016
c	0.09	0.25	0.004	0.010
D	2.80	3.00	0.110	0.118
E	1.50	1.80	0.059	0.071
e	0.95		0.037	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.20	0.30	0.008	0.012
x	-	0.20	-	0.008
y	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.60	-	0.024
e1	2.10		0.083	
l1	-	0.90	-	0.035

Dimension in mm / inches

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